

Smart Highside High Current Power Switch



Reversave™

 Reverse battery protection by self turn on of power MOSFET

Features

- Overload protection
- Current limitation
- Short circuit protection
- Overtemperature protection
- Overvoltage protection (including load dump)
- Clamp of negative voltage at output
- Fast deenergizing of inductive loads 1)
- Low ohmic inverse current operation
- Diagnostic feedback with load current sense
- Open load detection via current sense
- Loss of V_{bb} protection²⁾
- Electrostatic discharge (ESD) protection
- Green Product (RoHS compliant)
- AEC qualified

Application

- Power switch with current sense diagnostic feedback for 12 V and 24 V DC grounded loads
- Most suitable for loads with high inrush current like lamps and motors; all types of resistive and inductive loads
- Replaces electromechanical relays, fuses and discrete circuits

Product Summary

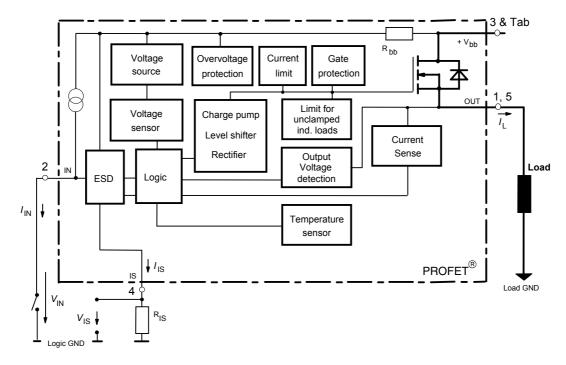
Overvoltage protection	V _{bb(AZ)}	62	V
Output clamp	$V_{\rm ON(CL)}$	44	V
Operating voltage	$V_{ m bb(on)}$	5.0 34	V
On-state resistance	RON	3.6	$m\Omega$
Load current (ISO)	<i>I</i> L(ISO)	115	Α
Short circuit current limitation	<i>I</i> L(SC)	220	Α
Current sense ratio	<i>I</i> L : <i>I</i> _{IS}	21000	

PG-TO218-5-146



General Description

N channel vertical power FET with charge pump, current controlled input and diagnostic feedback with load current sense, integrated in Smart SIPMOS® chip on chip technology. Providing embedded protective functions.



¹⁾ With additional external diode.

²⁾ Additional external diode required for energized inductive loads (see page 9).



Pin	Symbol	Function
1	OUT	Output to the load. The pins 1 and 5 must be shorted with each other especially in high current applications! ³⁾
2	IN	Input, activates the power switch in case of short to ground
3	Vbb	Positive power supply voltage, the tab is electrically connected to this pin. In high current applications the tab should be used for the V_{bb} connection instead of this pin ⁴⁾ .
4	IS	Diagnostic feedback providing a sense current proportional to the load current; zero current on failure (see Truth Table on page 7)
5	OUT	Output to the load. The pins 1 and 5 must be shorted with each other especially in high current applications! ³⁾

Maximum Ratings at $T_j = 25$ °C unless otherwise specified

Parameter	Symbol	Values	Unit
Supply voltage (see page 4 and 5)	$V_{ m bb}$	40	٧
Supply voltage for short circuit protection, $T_{j,\text{start}} = -40^{\circ}\text{C} \dots + 150^{\circ}\text{C}$: (E _{AS} limitation see diagram on page 10)	$V_{ m bb}$	34	V
Load current (short circuit current, see page 5)	<i>I</i> ∟	self-limited	Α
Load dump protection $V_{\text{LoadDump}} = U_{\text{A}} + V_{\text{S}}$, $U_{\text{A}} = 13.5 \text{ V}$			
$R_{\rm l}^{5)} = 2 \Omega$, $R_{\rm L} = 0.54 \Omega$, $t_{\rm d} = 200 \rm ms$,	V _{Load dump} 6)	80	V
IN, IS = open or grounded			
Operating temperature range	T _j	-40+150	°C
Storage temperature range	$T_{ m stg}$	-55+150	
Power dissipation (DC), T _C ≤ 25 °C	P_{tot}	360	W
Inductive load switch-off energy dissipation, single pulse $V_{bb} = 12V$, $T_{j,start} = 150^{\circ}C$, $T_{C} = 150^{\circ}C$ const., $I_{L} = 20$ A, $Z_{L} = 15$ mH, 0Ω , see diagram on page 10	E _{AS}	3	J
Electrostatic discharge capability (ESD) Human Body Model acc. MIL-STD883D, method 3015.7 and ESD assn. std. S5.1-1993, C = 100 pF, R = 1.5 k Ω	V _{ESD}	4	kV
Current through input pin (DC)	I _{IN}	+15, -250	mA
Current through current sense status pin (DC)	I _{IS}	+15, -250	
see internal circuit diagrams on page 8 and 9			

³⁾ Not shorting all outputs will considerably increase the on-state resistance, reduce the peak current capability and decrease the current sense accuracy

Otherwise add up to 0.5 m Ω (depending on used length of the pin) to the R_{ON} if the pin is used instead of the

⁵⁾ $R_{\rm I}$ = internal resistance of the load dump test pulse generator.

 $^{^{6)}}$ $\,$ $\,$ V $_{Load\ dump}$ is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839.



Thermal Characteristics

Parameter and Conditions		Symbol	Values			Unit
			min	typ	max	
Thermal resistance	chip - case:	R _{thJC} ⁷⁾			0.35	K/W
	Junction - ambient (free air):	R_{thJA}		30		

Electrical Characteristics

Parameter and Conditions	Symbol	Values		Unit	
at $T_j = -40 \dots +150 ^{\circ}\text{C}$, $V_{bb} = 12 ^{\circ}\text{V}$ unless otherwise specified		min	typ	max	·

Load Switching Capabilities and Characteristics

Load Switching Capabilities and Characteristics					
On-state resistance (Tab to pins 1,5, see measurement					
circuit page 8) $I_L = 20 \text{ A}, T_j = 25 ^{\circ}\text{C}$:	R_{ON}		2.8	3.6	$m\Omega$
$V_{IN} = 0$, $I_L = 20 \text{ A}$, $T_j = 150 ^{\circ}\text{C}$:			5.0	6.5	
$I_{L} = 120 \text{ A}, T_{j} = 150 ^{\circ}\text{C}$:				6.5	
$V_{bb} = 6V^{8}$, $I_{L} = 20 \text{ A}$, $T_{j} = 150 ^{\circ}\text{C}$:	R _{ON(Static)}		7	10	
Nominal load current ⁹⁾ (Tab to pins 1,5)	$I_{L(ISO)}$	90	115	-	Α
ISO 10483-1/6.7: $V_{ON} = 0.5 \text{V}$, $T_{C} = 85 ^{\circ}\text{C}^{-10}$					
Maximum load current in resistive range		000			
(Tab to pins 1,5) $V_{ON} = 1.8 \text{ V}, T_{C} = 25 ^{\circ}\text{C}$:	I _{L(Max)}	390			
see diagram on page 12 $V_{ON} = 1.8 \text{ V}, T_{C} = 150 ^{\circ}\text{C}$:		215			Α
Turn-on time ¹¹⁾ $I_{IN} \int to 90\% V_{OUT}$:	<i>t</i> on	120	250	600	μs
Turn-off time $I_{IN} \perp$ to 10% V_{OUT} :	$t_{ m off}$	40	90	150	
R_L =1 Ω , T_j =-40+150°C					
Slew rate on $^{11)}$ (10 to 30% V_{OUT})	d V/dt _{on}	0.2	0.5	8.0	V/μs
$R_L = 1 \Omega$, $T_j = 25$ °C					
Slew rate off ¹¹⁾ (70 to 40% V_{OUT})	-d V/dt _{off}	0.2	0.6	1	V/μs
$R_L = 1 \Omega$, $T_j = 25$ °C					

 $[\]begin{array}{ll} \hbox{7)} & \hbox{Thermal resistance R_{thCH} case to heatsink (about 0.25 K/W with silicone paste) not included!} \\ \end{array}$

B) Decrease of V_{bb} below 10 V causes a slowly a dynamic increase of R_{ON} to a higher value of $R_{ON(Static)}$. As long as $V_{bIN} > V_{bIN(u)\ max}$, R_{ON} increase is less than 10 % per second for $T_J < 85$ °C.

⁹⁾ not subject to production test, specified by design

 $T_{\rm J}$ is about 105°C under these conditions.

¹¹⁾ See timing diagram on page 13.



Data Sheet BTS550

Parameter and Conditions	Symbol	Values		Unit	
at $T_j = -40 \dots +150 ^{\circ}\text{C}$, $V_{bb} = 12 ^{\circ}\text{V}$ unless otherwise specified		min	typ	max	

Inverse Load Current Operation

On-state resistance (Pins 1,5 to pin 3)						
$V_{\text{bIN}} = 12 \text{ V}, I_{\text{L}} = -20 \text{ A}$	<i>T</i> _j =25 °C:	$R_{\rm ON(inv)}$		2.8	3.6	mΩ
see diagram on page 10	$T_{\rm j} = 150^{\circ}{\rm C}$:	, ,		5.0	6.5	
Nominal inverse load current (Pins 1,5 to Tab)		I _{L(inv)}	90	115		Α
$V_{\text{ON}} = -0.5 \text{V}, T_{\text{C}} = 85 ^{\circ} \text{C}^{10}$						
Drain-source diode voltage ($V_{out} > V_{bb}$) $I_L = -20 \text{ A}, I_{IN} = 0, T_j = +150 ^{\circ}\text{C}$		-V _{ON}		0.6	0.7	V

Operating Parameters

Operating voltage ($V_{IN} = 0$) 8, 12)	$V_{ m bb(on)}$	5.0		34	V
Undervoltage shutdown 13)		$V_{bIN(u)}$	1.5	3.0	4.5	V
Undervoltage start of charge posee diagram page 14	ump	$V_{ m blN(ucp)}$	3.0	4.5	6.0	V
Overvoltage protection ¹⁴⁾	<i>T</i> _j =-40°C:	$V_{bIN(Z)}$	60			V
$I_{bb} = 15 \mathrm{mA}$	$T_{\rm j}$ = 25+150°C:		62	64		
Standby current	<i>T</i> _j =-40+25°C:	I _{bb(off)}		15	25	μΑ
$I_{IN} = 0$	$T_{\rm j} = 150^{\circ}{\rm C}$:			25	50	

¹²⁾ If the device is turned on before a V_{bb} -decrease, the operating voltage range is extended down to $V_{bIN(u)}$. For all voltages 0 ... 34 V the device provides embedded protection functions against overtemperature and short circuit.

¹³⁾ $V_{bIN} = V_{bb} - V_{IN}$ see diagram on page 8. When V_{bIN} increases from less than $V_{bIN(u)}$ up to $V_{bIN(ucp)} = 5 \text{ V}$ (typ.) the charge pump is not active and $V_{OUT} \approx V_{bb} - 3 \text{ V}$.

¹⁴⁾ See also $V_{\text{ON(CL)}}$ in circuit diagram on page 9.



Data Sheet BTS550

Parameter and Conditions	Symbol			Unit	
at $T_j = -40 \dots +150 ^{\circ}\text{C}$, $V_{bb} = 12 ^{\circ}\text{V}$ unless otherwise specified		min	typ	max	
Protection Functions ¹⁵⁾					
Short circuit current limit (Tab to pins 1,5) ¹⁶					
$V_{ON} = 12 \text{ V}$, time until shutdown max. 350 µs $T_c = -40^{\circ}\text{C}$:	I _{L(SCp)}	100	190	350	Α
$T_{\rm c}$ =25°C:		110	220	330	
$T_{\rm c}$ =+150°C:		120	210	310	
Short circuit shutdown delay after input current positive slope, $V_{\rm ON} > V_{\rm ON(SC)}$ min. value valid only if input "off-signal" time exceeds 30 μ s	$t_{ m d(SC)}$	80		350	μs
Output clamp ¹⁷)	- V _{OUT(CL)}	14	17	20	V
Output clamp (inductive load switch off) at $V_{\text{OUT}} = V_{\text{bb}} - V_{\text{ON(CL)}}$ (e.g. overvoltage) $I_{\text{L}} = 40 \text{ mA}$	V _{ON(CL)}	40	44	47	V
Short circuit shutdown detection voltage (pin 3 to pins 1,5)	V _{ON(SC)}		6		V
Thermal overload trip temperature	$T_{\rm jt}$	150			°C
Thermal hysteresis	$\Delta T_{\rm jt}$		10		K

Reverse Battery

Reverse battery voltage 18)		- V _{bb}		-	32	V
On-state resistance (Pins 1,5 to pin 3)	$T_j = 25$ °C:	R _{ON(rev)}		3.4	4.3	mΩ
$V_{\rm bb}$ =-12V, $V_{\rm IN}$ =0, $I_{\rm L}$ =-20A, $R_{\rm IS}$ =1 k Ω	$T_{\rm j} = 150^{\circ}{\rm C}$:	, ,			7.5	
Integrated resistor in V _{bb} line	T _j =25°C:	R _{bb}	90	110	135	Ω
	T _j =150°C:		105	125	150	

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¹⁵) Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

¹⁶) Short circuit is a failure mode. The device is not designed to operate continuously into a short circuit by permanent resetting the short circuit latch function. The lifetime will be reduced under such conditions.

¹⁷⁾ This output clamp can be "switched off" by using an additional diode at the IS-Pin (see page 8). If the diode is used, V_{OUT} is clamped to V_{bb}- V_{ON(CL)} at inductive load switch off.

The reverse load current through the intrinsic drain-source diode has to be limited by the connected load (as it is done with all polarity symmetric loads). Note that under off-conditions ($I_{IN} = I_{IS} = 0$) the power transistor is not activated. This results in raised power dissipation due to the higher voltage drop across the intrinsic drain-source diode. The temperature protection is not active during reverse current operation! Increasing reverse battery voltage capability is simply possible as described on page 9.



Data Sheet BTS550

Parameter and Conditions	Symbol	Values		Unit	
at $T_j = -40 \dots +150 ^{\circ}\text{C}$, $V_{bb} = 12 ^{\circ}\text{V}$ unless otherwise specified		min	typ	max	·
Diagnostic Characteristics					
Current sense ratio, static on-condition, $T_j = 25^{\circ}\text{C}$: $K_{\text{ILIS}} = I_{\text{L}} : I_{\text{IS}}$, $T_j = 150^{\circ}\text{C}$: $K_{\text{ILIS}} = I_{\text{L}} : I_{\text{IS}}$, $T_j = 150^{\circ}\text{C}$: $V_{\text{ON}} < 1.5 \text{V}^{19}$), $I_{\text{L}} = 20 \text{A}$, $T_j = -40^{\circ}\text{C}$: $V_{\text{IS}} < V_{\text{OUT}} - 5 \text{V}$, $T_j = 25^{\circ}\text{C}$: $T_j = 150^{\circ}\text{C}$: see diagram on page 11 $I_{\text{L}} = 12 \text{A}$, $T_j = -40^{\circ}\text{C}$: $T_j = 25^{\circ}\text{C}$: $T_j = 150^{\circ}\text{C}$: $T_j $	<i>k</i> _{ILIS}	19 000 18 000 18 500 18 500 18 000 16 000 17 000 17 500 12 000 14 000	20 600 20 500 19 000 22 300 21 400 19 500 23 500 22 000 19 900 28 000 24 000 20 500	22 500 21 500 26 000 25 000 23 000 30 000 26 500 24 500 46 000 34 000	
Sense current saturation	I _{IS,lim}	6.5			mA
Current sense leakage current					
$I_{\text{IN}} = 0$:	I _{IS(LL)}			0.5	μΑ
$V_{\text{IN}} = 0, \ I_{\text{L}} \leq 0$:	I _{IS(LH)}		2		
Current sense settling time ²⁰⁾	$t_{\rm s(IS)}$			500	μs
Overvoltage protection $T_j = -40^{\circ}\text{C}$:	$V_{bIS(Z)}$	60			V
$I_{bb} = 15 \text{ mA}$ $T_j = 25+150^{\circ}\text{C}$:		62	64		
Input					
Input and operating current (see diagram page 12) IN grounded (V _{IN} = 0)	I _{IN(on)}		0.8	1.5	mA
Input current for turn-off ²¹⁾	I _{IN(off)}			80	μΑ

¹⁹⁾ If V_{ON} is higher, the sense current is no longer proportional to the load current due to sense current saturation, see $I_{IS,lim}$.

²⁰⁾ not subject to production test, specified by design

We recommend the resistance between IN and GND to be less than 0.5 $k\Omega$ for turn-on and more than 500 $k\Omega$ for turn-off. Consider that when the device is switched off (I_{IN} = 0) the voltage between IN and GND reaches almost V_{bb}.



Truth Table

	Input current	Output	Current Sense	Remark
	level	level	l _{IS}	
Normal	L	L	0	
operation	Н	Н	nominal	=I _L / k _{ilis} , up to I _{IS} =I _{IS,lim}
Very high load current	Н	Н	I _{IS, lim}	up to V _{ON} =V _{ON(Fold back)} I _{IS} no longer proportional to I _L
Current- limitation	н	Н	0	$V_{ON} > V_{ON(Fold back)}$ if $V_{ON} > V_{ON(SC)}$, shutdown will occure
Short circuit to	L	L	0	
GND	Н	L	0	
Over-	L	L	0	
temperature	Н	L	0	
Short circuit to	L	Н	0	
V_{bb}	Н	Н	<nominal <sup="">22)</nominal>	
Open load	L	Z ²³)	0	
	Н	Н	0	
Negative output voltage clamp	L	L	0	
Inverse load	L	Н	0	
current	Н	Н	0	

L = "Low" Level H = "High" Level

Options Overview

Type BTS	550P
Overtemperature protection with hysteresis	Х
$T_{\rm j}$ >150 °C, latch function ²⁴)	
$T_{\rm j}$ >150 °C, with auto-restart on cooling	X
Short circuit to GND protection	
with overtemperature shutdown	
switches off when $V_{\rm ON}>6$ V typ. (when first turned on after approx. 180 μ s)	X
Overvoltage shutdown	-
Output negative voltage transient limit	
to V _{bb} - V _{ON(CL)}	X
to $V_{OUT} = -19 \text{ V typ}$	X ²⁵⁾

Overtemperature reset by cooling: $T_i < T_{it}$ (see diagram on page 14)

Short circuit to GND: Shutdown remains latched until next reset via input (see diagram on page 13)

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Low ohmic short to $V_{\rm bb}$ may reduce the output current $I_{\rm L}$ and can thus be detected via the sense current $I_{\rm IS}$.

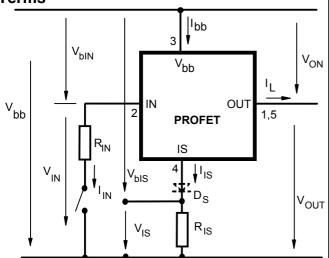
²³⁾ Power Transistor "OFF", potential defined by external impedance.

Latch except when $V_{\rm bb}$ - $V_{\rm OUT}$ < $V_{\rm ON(SC)}$ after shutdown. In most cases $V_{\rm OUT}$ = 0 V after shutdown ($V_{\rm OUT}$ \neq 0 V only if forced externally). So the device remains latched unless $V_{\rm bb}$ < $V_{\rm ON(SC)}$ (see page 5). No latch between turn on and $t_{\rm d(SC)}$.

²⁵⁾ Can be "switched off" by using a diode D_S (see page 8) or leaving open the current sense output.

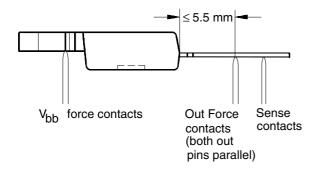


Terms

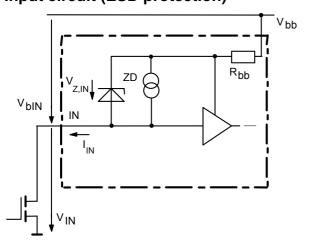


Two or more devices can easily be connected in parallel to increase load current capability.

RON measurement layout

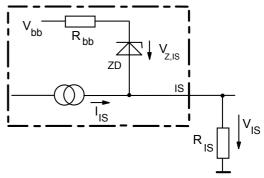


Input circuit (ESD protection)



When the device is switched off ($I_{IN} = 0$) the voltage between IN and GND reaches almost V_{bb} . Use a mechanical switch, a bipolar or MOS transistor with appropriate breakdown voltage as driver. $V_{Z,IN} = 64 \text{ V (typ)}$.

Current sense status output



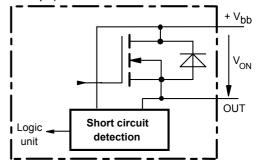
 $V_{\rm Z,IS}$ = 64 V (typ.), $R_{\rm IS}$ = 1 k Ω nominal (or 1 k Ω /n, if n devices are connected in parallel). $I_{\rm S}$ = $I_{\rm L}/k_{\rm ilis}$ can be driven only by the internal circuit as long as $V_{\rm out}$ - $V_{\rm IS}$ > 5 V. If you want to measure load currents up

to $I_{L(M)}$, R_{IS} should be less than $\frac{V_{\rm bb}$ - 5 V}{I_{L(M)} / $K_{\rm ilis}$.

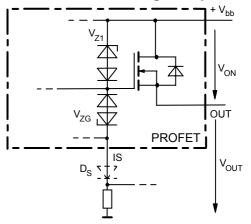
Note: For large values of $R_{\rm IS}$ the voltage $V_{\rm IS}$ can reach almost $V_{\rm bb}$. See also overvoltage protection. If you don't use the current sense output in your application, you can leave it open.

Short circuit detection

Fault Condition: $V_{ON} > V_{ON(SC)}$ (6 V typ.) and t> $t_{d(SC)}$ (80 ...350 µs).



Inductive and overvoltage output clamp

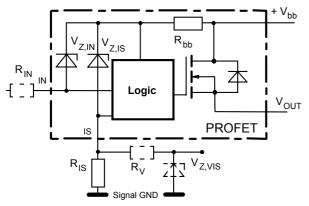


 V_{ON} is clamped to $V_{ON(Cl)} = 42 \, \text{V}$ typ. At inductive load switch-off without D_S , V_{OUT} is clamped to



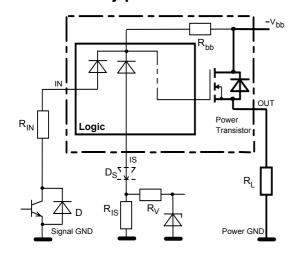
 $V_{OUT(CL)} = -19 V$ typ. via V_{ZG} . With D_S , V_{OUT} is clamped to V_{bb} - $V_{ON(CL)}$ via V_{Z1} . Using D_S gives faster deenergizing of the inductive load, but higher peak power dissipation in the PROFET. In case of a floating ground with a potential higher than 19V referring to the OUT - potential the device will switch on, if diode DS is not used.

Overvoltage protection of logic part



 $R_{bb} = 120 \Omega \text{ typ.}, \ V_{Z,IN} = V_{Z,IS} = 64 \text{ V typ.}, \ R_{IS} = 1 \text{ k}\Omega$ nominal. Note that when overvoltage exceeds 69 V typ. a voltage above 5V can occur between IS and GND, if R_V, V_{Z,VIS} are not used.

Reverse battery protection



 $R_V \ge 1 \text{ k}\Omega$, $R_{IS} = 1 \text{ k}\Omega$ nominal. Add R_{IN} for reverse battery protection in applications with V_{bb} above

16 V¹⁸⁾; recommended value:
$$\frac{1}{R_{\text{IN}}} + \frac{1}{R_{\text{IS}}} + \frac{1}{R_{\text{V}}} = \frac{0.1 \text{A}}{|V_{\text{bb}}| - 12 \text{V}}$$
 if D_S is not used (or $\frac{1}{R_{\text{IN}}} = \frac{0.1 \text{A}}{|V_{\text{bb}}| - 12 \text{V}}$ if

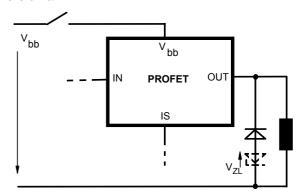
$$\frac{0.1A}{|V_{bb}| - 12V}$$
 if D_S is not used (or $\frac{1}{R_{IN}} = \frac{0.1A}{|V_{bb}| - 12V}$ if D_S is used).

To minimize power dissipation at reverse battery operation, the summarized current into the IN and IS pin should be about 120mA. The current can be provided by using a small signal diode D in parallel to the input switch, by using a MOSFET input switch or by proper adjusting the current through $R_{\rm IS}$ and R_{V} .

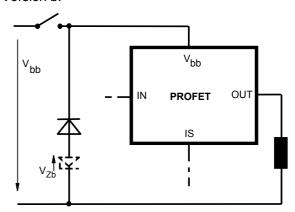
V_{bb} disconnect with energized inductive load

Provide a current path with load current capability by using a diode, a Z-diode, or a varistor. (V_{ZL} < 72 V or V_{Zb} < 30 V if R_{IN}=0). For higher clamp voltages currents at IN and IS have to be limited to 250 mA.

Version a:

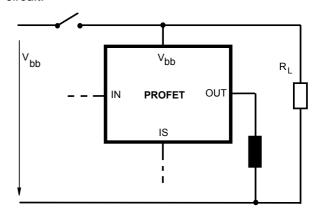


Version b:



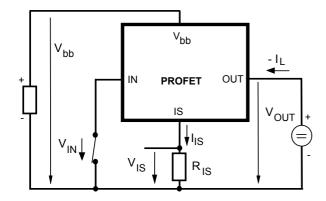
Note that there is no reverse battery protection when using a diode without additional Z-diode V_{ZL},

Version c: Sometimes a neccessary voltage clamp is given by non inductive loads R_I connected to the same switch and eliminates the need of clamping circuit:



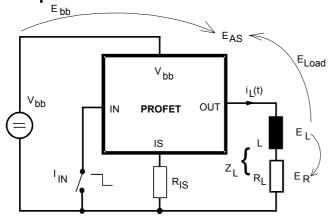


Inverse load current operation



The device is specified for inverse load current operation ($V_{\rm OUT} > V_{\rm bb} > {\bf 0V}$). The current sense feature is not available during this kind of operation ($I_{\rm IS} = 0$). With $I_{\rm IN} = 0$ (e.g. input open) only the intrinsic drain source diode is conducting resulting in considerably increased power dissipation. If the device is switched on ($V_{\rm IN} = 0$), this power dissipation is decreased to the much lower value $R_{\rm ON(INV)}$ * f (specifications see page 4). Note: Temperature protection during inverse load current operation is not possible!

Inductive load switch-off energy dissipation



Energy stored in load inductance:

$$E_{\rm L} = {}^{1}/_{2} \cdot {\rm L} \cdot {\rm I}_{\rm L}^{2}$$

While demagnetizing load inductance, the energy dissipated in PROFET is

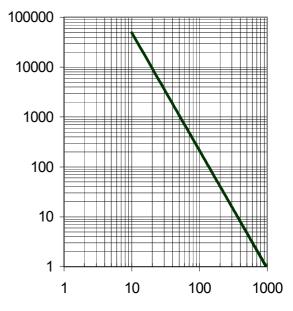
$$E_{AS} = E_{bb} + E_L - E_R = \int V_{ON(CL)} \cdot i_L(t) dt$$

with an approximate solution for $R_L > 0\,\Omega$:

$$E_{AS} = \frac{I_{L} \cdot L}{2 \cdot R_{L}} \left(V_{bb} + |V_{OUT(CL)}| \right) ln \left(1 + \frac{I_{L} \cdot R_{L}}{|V_{OUT(CL)}|} \right)$$

Maximum allowable load inductance for a single switch off

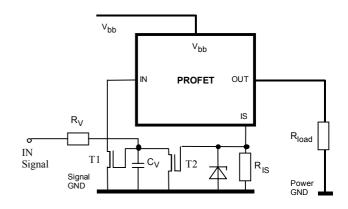
$$L = f(I_L)$$
; T_{j,start} = 150°C, V_{bb} = 12 V, R_L = 0 Ω
L [μ H]



I_L [Α]

Externally adjustable current limit

If the device is conducting, the sense current can be used to reduce the short circuit current and allow higher lead inductance (see diagram above). The device will be turned off, if the threshold voltage of T2 is reached by $\rm I_s{}^*R_{\rm is}$. After a delay time defined by $\rm R_v{}^*C_v$ T1 will be reset. The device is turned on again, the short circuit current is defined by $\rm I_{L(SC)}$ and the device is shut down after $\rm t_{d(SC)}$ with latch function.

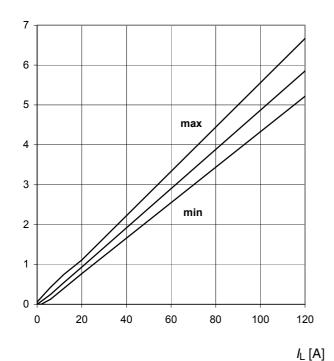




Characteristics

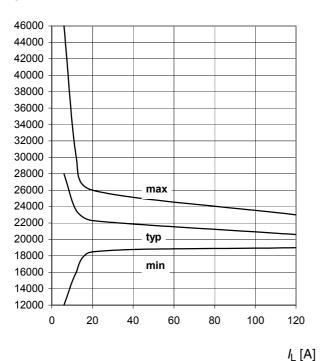
Current sense versus load current:

 $I_{IS} = f(I_L)$ $I_{IS} [mA]$



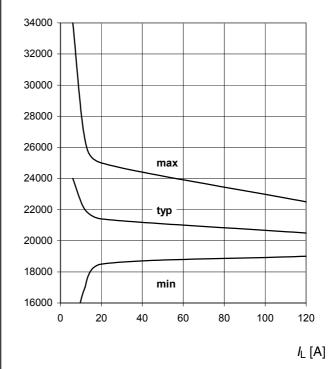
Current sense ratio:

 $K_{\text{ILIS}} = f(I_{\text{L}}), T_{\text{J}} = -40 \text{ }^{\circ}\text{C}$ K_{IIIS}



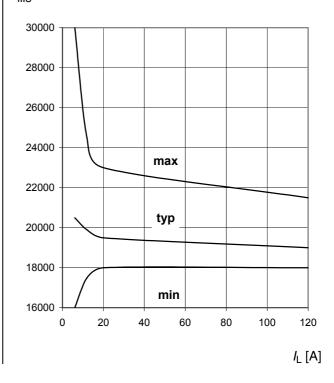
Current sense ratio:

 $K_{\text{ILIS}} = f(I_{\text{L}}), T_{\text{J}} = 25 \,^{\circ}\text{C}$



Current sense ratio:

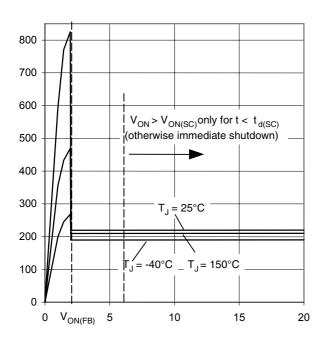
 $K_{\text{ILIS}} = f(I_{\text{L}}), T_{\text{J}} = 150 \text{ }^{\circ}\text{C}$ K_{illis}





Typ. current limitation characteristic $I_L = f(V_{ON}, T_i)$

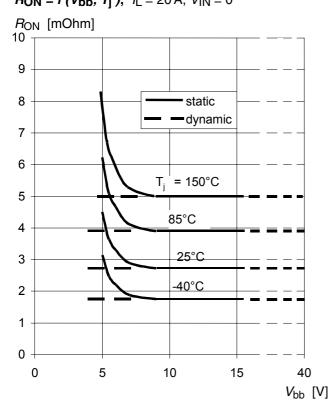
/∟ [A]



Von [V]

In case of $V_{ON} > V_{ON(SC)}$ (typ. 6 V) the device will be switched off by internal short circuit detection.

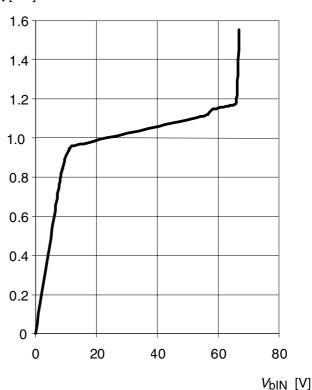
Typ. on-state resistance $R_{ON} = f(V_{bb}, T_i)$; $I_L = 20 \text{ A}$; $V_{IN} = 0$



Typ. input current

 $I_{\text{IN}} = f(V_{\text{bIN}}), V_{\text{bIN}} = V_{\text{bb}} - V_{\text{IN}}$

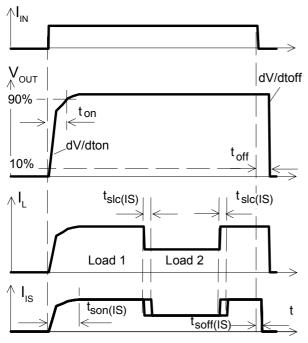
IN [mA]





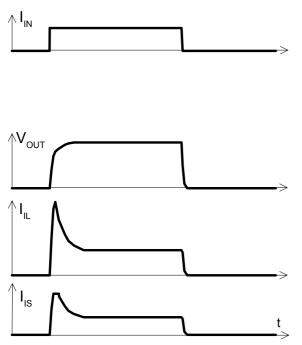
Timing diagrams

Figure 1: Switching a resistive load, change of load current in on-condition:



The sense signal is not valid during a settling time after turn-on/off and after change of load current.

Figure 2a: Switching motors and lamps:



Sense current saturation can occur at very high inrush currents (see $I_{\text{IS,lim}}$ on page 6).

Figure 2b: Switching an inductive load:

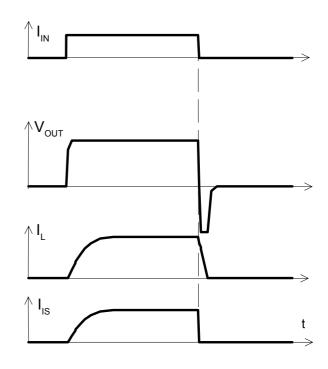
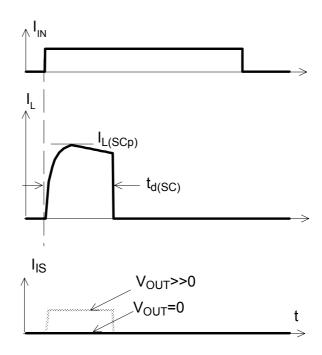


Figure 3: Short circuit: shut down by short circuit detection, reset by $I_{IN} = 0$.



Shut down remains latched until next reset via input.



Figure 4: Overtemperature Reset if $T_j < T_{jt}$

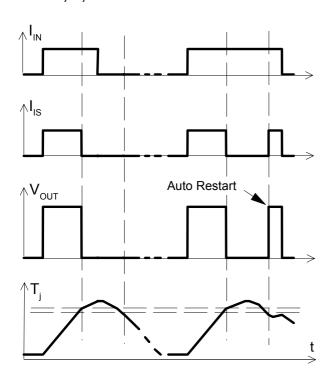
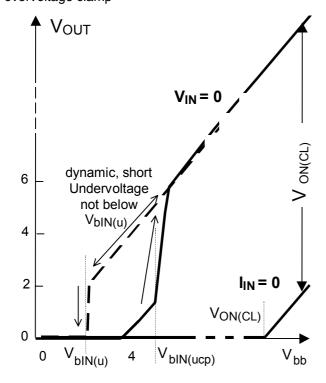


Figure 5: Undervoltage restart of charge pump, overvoltage clamp

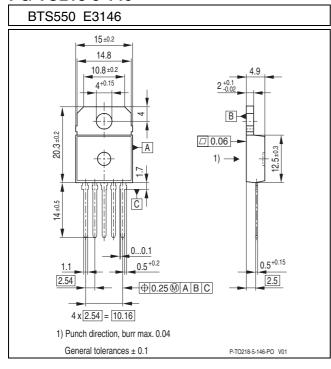




Package Dimensions

All dimensions in mm

PG-TO218-5-146



Green Product

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pb-free finish on leads).

Revision History

Version	Changes		
2010-June-01	RoHS-compliant version of BTS550 Page 1, page 15: RoHS compliance statement and Green product feature added Page 2: pin marking removed. Page 7: Options overview reduced.		
	Package drawing updated Revision history added Legal disclaimer updated		

Edition 2010-06-01
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Infineon Technologies AG
81726 Munich, Germany
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